

IN THE CLAIMS:

Please amend the claims to read as follows:

B2
5. (Twice Amended) A method of manufacturing a DRAM-incorporated semiconductor device in which a DRAM section and a logic section are formed on a semiconductor substrate that is isolated into elements, said method comprising:

forming a metal film directly on surfaces of source-drain regions and gate regions in said DRAM section and said logic section; and

heat treating said device to react said metal film with said surfaces to concurrently form a metal silicide layer in each of said DRAM section and said logic section.

B3
12. (Twice Amended) A method of manufacturing a semiconductor device having a memory cell section and an adjacent circuit section, said method comprising:

forming a metal film directly on surfaces of source-drain regions and gate regions in said memory cell section and said adjacent circuit section; and

annealing said device to react said metal film with said surfaces to concurrently form a metal silicide layer in each of said memory cell section and said adjacent circuit section.

B4
15. (Amended) A method of manufacturing a semiconductor device comprising:
forming a metal film on source-drain and gate surfaces in a memory cell section of a substrate, and on source-drain and gate surfaces in an adjacent circuit section of said substrate; and

heat treating said device to react said metal film with silicon in said surfaces to concurrently form a metal silicide layer in each of said memory cell section and said adjacent circuit section.